



N- and P-Channel 2.5-V (G-S) MOSFET

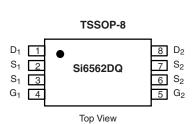
PRODUCT SUMMARY				
	V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
N-Channel	20	0.030 at V _{GS} = 4.5 V	± 4.5	
		0.040 at V _{GS} = 2.5 V	± 3.9	
P-Channel	- 20	0.050 at V _{GS} = - 4.5 V	± 3.5	
		0.085 at V _{GS} = - 2.5 V	± 2.7	

FEATURES

- Halogen-free Option Available
- TrenchFET® Power MOSFETS: 2.5 V Rated

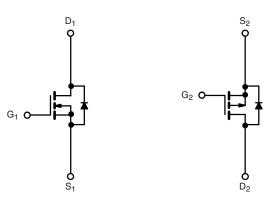


RoHS'



Ordering Information: Si6562DQ-T1

Si6562DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage		V_{DS}	20	- 20	V	
Gate-Source Voltage		V_{GS}	± 12	± 12		
Continuous Drain Courset /T 150 00/8	T _A = 25 °C	- I _D	± 4.5	± 3.5		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		± 3.6	± 2.7		
Pulsed Drain Current		I _{DM}	± 30	± 30	Α Α	
Continuous Source Current (Diode Conduction) ^a		I _S	1.25	- 1.25		
Maximum Power Dissipation ^a	T _A = 25 °C	P _D 1.0		0	w	
	T _A = 70 °C	'D	0.64] **	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	N- or P-Channel	Unit
Maximum Junction-to-Ambient ^a	R _{thJA}	125	°C/W

Notes:

a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

Si6562DQ

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SPECIFICATIONS $T_J = 25 ^{\circ}C$	Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
Static		1301 001121110110			.,,,,		-	
Gate Threshold Voltage	.,	$V_{DS} = V_{GS}, I_D = 250 \mu A$	N-Ch	0.6				
	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.6			V	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V	N-Ch			± 100	nA	
			P-Ch			± 100		
Zava Cata Valtaga Dvain Cuwant	,	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	N-Ch			1		
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$	P-Ch			- 1	μA 25	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	N-Ch			25		
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			- 25		
On-State Drain Current ^a		$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	N-Ch	30			А	
	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	P-Ch	- 30				
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 4.5 \text{ A}$	N-Ch		0.023	0.030		
		V _{GS} = - 4.5 V, I _D = - 3.5 A	P-Ch		0.040	0.050	Ω	
		$V_{GS} = 2.5 \text{ V}, I_D = 3.9 \text{ A}$	N-Ch		0.030	0.040		
		V _{GS} = - 2.5 V, I _D = - 2.7 A	P-Ch		0.060	0.085		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 4.5 A	N-Ch		20		S	
		V _{DS} = - 10 V, I _D = - 3.5 A	P-Ch		10			
	V _{SD}	I _S = 1.25 A, V _{GS} = 0 V	N-Ch		0.65	1.2	.,	
Diode Forward Voltage ^a		I _S = - 1.25 A, V _{GS} = 0 V	P-Ch		0.72	- 1.2	V	
Dynamic ^b							•	
Total Gate Charge	Qg		N-Ch		13	25		
Total date onlinge	Qg	N-Channel $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 4.5 \text{ A}$	P-Ch		14.5	25	nC	
Gate-Source Charge	Q_{gs}		N-Ch		3.0			
<u> </u>		P-Channel	P-Ch		3.5			
Gate-Drain Charge	Q _{gd}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.5 \text{ A}$	N-Ch P-Ch		3.3 3.5			
			N-Ch		22	50		
Turn-On Delay Time	t _{d(on)}	N-Channel V_{DD} = 10 V, R_L = 10 Ω	P-Ch		27	50		
Rise Time	t _r		N-Ch		40	80		
		$I_D \cong 1 \text{ A, } V_{GEN} = 10 \text{ V, } R_G = 6 \Omega$	P-Ch		30	60		
Turn-Off Delay Time	t _{d(off)}	P-Channel	N-Ch		50	100	1	
		$V_{DD} = -10 \text{ V}, R_L = 10 \Omega$	P-Ch		57	100	ns	
		$I_D\cong$ - 1 A, $V_{GEN}=$ - 10 V, $R_G=6~\Omega$	N-Ch		20	40		
-	<u> </u>	1 25 4 11/11 252 27	P-Ch		21	40		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 1.25 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$	N-Ch		30	60		
Coality Line Coality Line		I _F = - 1.25 A, dI/dt = 100 A/μs	P-Ch		60	100		

Notes:

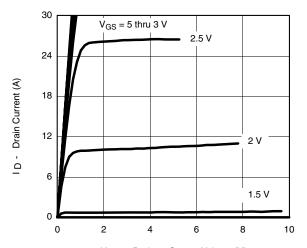
- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

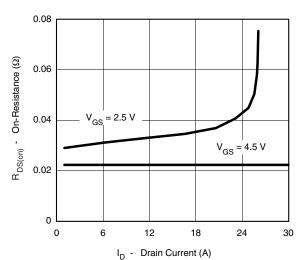




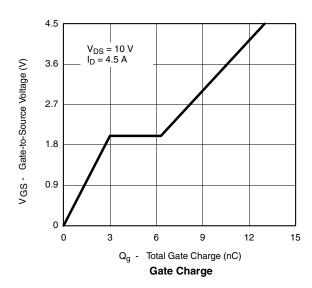
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

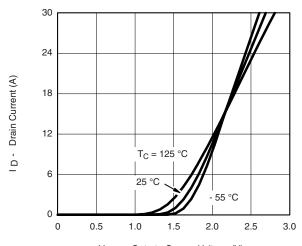


 V_{DS} - Drain-to-Source Voltage (V) **Output Characteristics**

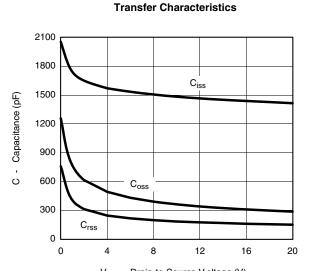


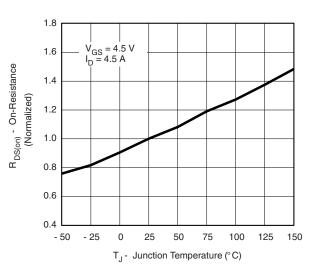
On-Resistance vs. Drain Current





 $V_{\mbox{\footnotesize GS}}$ - $\mbox{\ \ Gate-to-Source Voltage}$ (V)



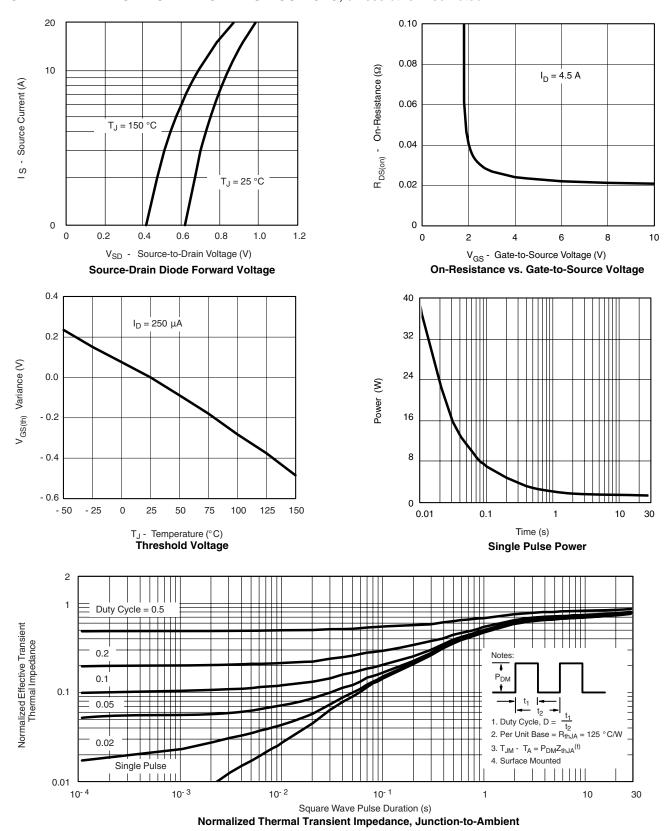


On-Resistance vs. Junction Temperature

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N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

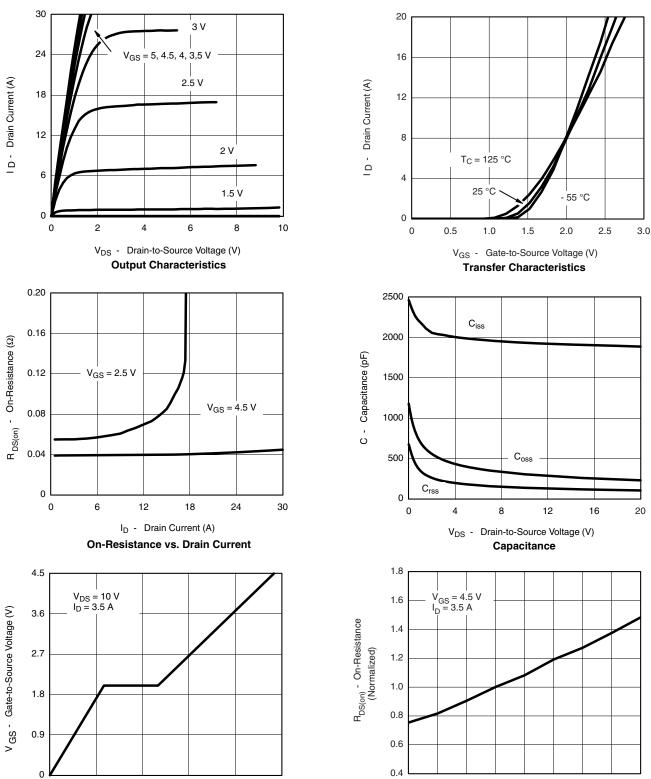








P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



- 50

- 25

25

50

 $\rm T_J$ - Junction Temperature (°C) On-Resistance vs. Junction Temperature

75

100

0

9

Total Gate Charge (nC)

Gate Charge

12

15

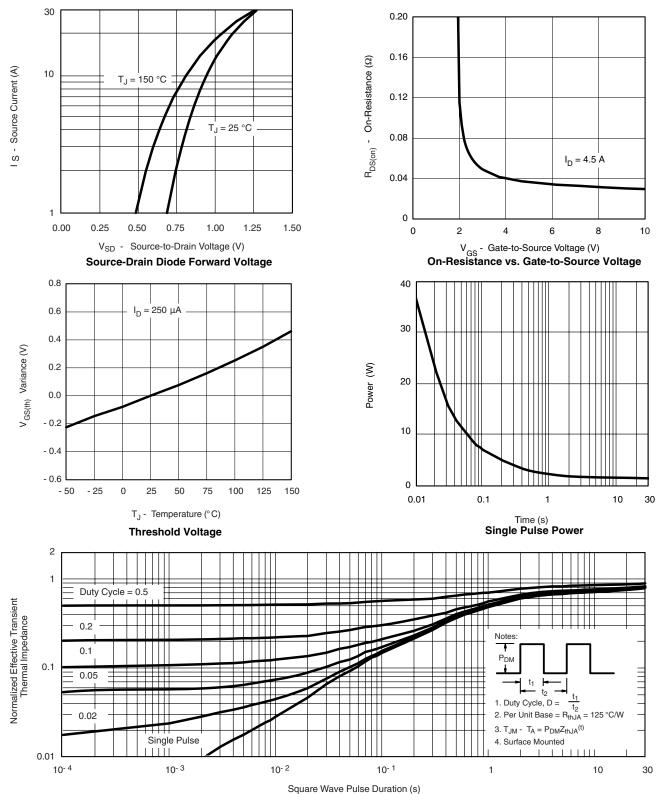
125

150

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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

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